









ESD2CAN24-Q1

# ESD2CAN24-Q1 Automotive 24-V, 2-Channel ESD Protection Diode for In-Vehicle **Networks**

#### 1 Features

- IEC 61000-4-2 level 4 ESD protection:
  - ±30-kV contact discharge
  - ±30-kV air-gap discharge
- ISO 10605 (330 pF, 330 Ω) ESD protection:
  - ±30-kV contact discharge
  - ±30-kV air-gap discharge
- Tested in compliance to IEC 61000-4-5
- 24 V working voltage
- Bidirectional ESD protection
- 2-channel device provides complete ESD protection with single component
- Low clamping voltage protects downstream components
- AEC-Q101 qualified
- I/O capacitance = 3 pF (typical)
- SOT-23 (DBZ) small, standard, common footprint
- SOT-323, SC-70 (DCK) very small, standard, space saving, common footprint
- Leaded packages used for automatic optical inspection (AOI)

## 2 Applications

- · Automotive in-vehicle networks:
  - Controller area network (CAN)
  - Controlled area network flexible data-rate (CAN-FD)
  - Low, fault tolerant CAN
  - High-speed CAN
- Industrial control networks:
  - DeviceNet IEC 62026-3
  - CANopen CiA 301/302-2 and EN 50325-4

## 3 Description

The ESD2CAN24-Q1 is a bidirectional ESD protection diode for Controller Area Network (CAN) interface protection. The ESD2CAN24-Q1 is rated to dissipate contact ESD strikes beyond the maximum level specified in the ISO 10605 automotive standard (±30-kV Contact, ±30-kV Airgap). The low dynamic resistance and low clamping voltage ensures system level protection against transient events. This protection is key as automotive systems require a high level of robustness and reliability for safety applications.

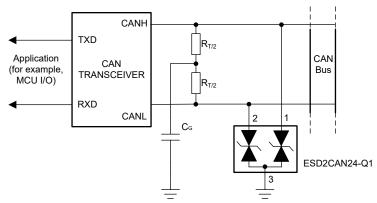
This device features a low IO capacitance per channel and a pin-out to suit two automotive CAN bus lines (CANH and CANL) from the damage caused by ElectroStatic Discharge (ESD) and other transients. Additionally, the 3 pF line capacitance of the ESD2CAN24-Q1 is suitable for CAN, CANFD. CAN SiC, and CAN-XL applications that can support data rates up to 10 Mbps.

The ESD2CAN24-Q1 is offered in two packages for easy flow through routing.

#### Device Information(1)

PART NUMBER	PACKAGE	BODY SIZE (NOM)
ESD2CAN24-Q1	SOT-23 (3)	2.92 mm × 1.30 mm
LODZCANZ4-QT	SOT-323, SC-70 (3)	2.00 mm × 1.25 mm

For all available packages, see the orderable addendum at the end of the data sheet.



**ESD2CAN24-Q1 Typical Application** 



## **Table of Contents**

1 Features1	7.4 Device Functional Modes	8
2 Applications 1	8 Application and Implementation	9
3 Description1	8.1 Application Information	
4 Revision History2	8.2 Typical Application	
5 Pin Configuration and Functions3	9 Power Supply Recommendations	
6 Specifications4	10 Layout	.10
6.1 Absolute Maximum Ratings4	10.1 Layout Guidelines	
6.2 ESD Ratings—AEC Specification4	10.2 Layout Example	
6.3 ESD Ratings—IEC Specification4	11 Device and Documentation Support	. <b>1</b> 1
6.4 ESD Ratings - ISO Specification4	11.1 Documentation Support	.11
6.5 Recommended Operating Conditions4	11.2 Receiving Notification of Documentation Updates	. 11
6.6 Thermal Information4	11.3 Support Resources	.11
6.7 Electrical Characteristics5	11.4 Trademarks	. 11
6.8 Typical Characteristics6	11.5 Electrostatic Discharge Caution	. 11
7 Detailed Description7	11.6 Glossary	. 11
7.1 Overview7	12 Mechanical, Packaging, and Orderable	
7.2 Functional Block Diagram7	Information	. 11
7.3 Feature Description7	12.1 Tape and Reel Information	.18
•	•	

## **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

## Changes from Revision \* (April 2022) to Revision A (June 2022)

**Page** 



# **5 Pin Configuration and Functions**

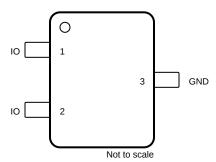


Figure 5-1. DCK and DBZ Package, 3-Pin SOT (Top View)

**Table 5-1. Pin Functions** 

PIN		TYPE(1)	DESCRIPTION	
NAME	NO.	1166	DESCRIPTION	
Ю	1, 2	I/O	ESD protected IO	
GND	3	_	Connect to ground.	

(1) I/O = Input or Output,



## **6 Specifications**

## 6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Peak pulse	IEC 61000-4-5 Power (t <sub>p</sub> - 8/20 μs) at 25°C		147	W
Peak pulse	IEC 61000-4-5 current (t <sub>p</sub> - 8/20 μs) at 25°C		6	А
T <sub>A</sub>	Operating free-air temperature	-55	150	°C
TJ	Junction temperature	-55	150	°C
T <sub>stg</sub>	Storage temperature	-65	155	°C

<sup>(1)</sup> Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If briefly operating outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.

## 6.2 ESD Ratings—AEC Specification

			VALUE	UNIT
V	Electrostatic discharge	Human body model (HBM), per AEC Q101-001	± 2500	V
V <sub>(ESD)</sub>	Electrostatic discharge	Charged device model (CDM), per AEC Q101-005	± 1000	<b>v</b>

## 6.3 ESD Ratings—IEC Specification

			VALUE	UNIT
V <sub>(ESD)</sub> Electrostatic discharge	IEC 61000-4-2 Contact Discharge, all pins	±30000	\/	
V(ESD)		IEC 61000-4-2 Air-gap Discharge, all pins	±30000	v

## 6.4 ESD Ratings - ISO Specification

				VALUE	UNIT
		ISO 10605, 150-pF, 330-Ω, IO	Contact discharge	± 30000	
	Electrostatic discharge		Air-gap discharge	± 30000	.,
V <sub>(ESD)</sub>	Electrostatic discriarge		Contact discharge	± 30000	v
		ISO 10605, 330-pF, 330-Ω, IO	Air-gap discharge	± 30000	

## **6.5 Recommended Operating Conditions**

		MIN	NOM MAX	UNIT
V <sub>IN</sub>	Input voltage	-24	24	V
T <sub>A</sub>	Operating free-air temperature	-55	150	°C

#### 6.6 Thermal Information

THERMAL METRIC <sup>(1)</sup>		ESD2C		
		DBZ (SOT-23)	DCK (SOT-323, SC-70)	UNIT
		3 PINS	3PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	291.5	283.0	°C/W
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	147.1	164.1	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	131.1	105.1	°C/W
$\Psi_{JT}$	Junction-to-top characterization parameter	32.0	67.1	°C/W

Submit Document Feedback

Copyright © 2022 Texas Instruments Incorporated



## 6.6 Thermal Information (continued)

THERMAL METRIC <sup>(1)</sup>		ESD2CA		
		DBZ (SOT-23)	DCK (SOT-323, SC-70)	UNIT
		3 PINS	3PINS	
Ψ <sub>JB</sub> Junction-to-board characterization parameter		130.2	104.4	°C/W
R <sub>θJC(bot)</sub>	Junction-to-case (bottom) thermal resistance	N/A	N/A	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

#### 6.7 Electrical Characteristics

over T<sub>A</sub> = 25°C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
V <sub>RWM</sub>	Reverse stand-off voltage		-24		24	V
$V_{BRF}$	Forward breakdown voltage, any IO pin to GND <sup>(1)</sup>	I <sub>IO</sub> = 1 mA	25.5	27.5	29.5	V
$V_{BRR}$	Reverse breakdown voltage, any IO pin to GND <sup>(1)</sup>	I <sub>IO</sub> = -1 mA	-29.5	-27.5	-25.5	V
	Clamping voltage <sup>(3)</sup>	$I_{PP}$ = 3.5 A, $t_p$ = 8/20 $\mu$ s, from IO to GND		31	42	
$V_{CLAMP}$	CLAMP	$I_{PP}$ = 6 A, $t_p$ = 8/20 $\mu$ s, from IO to GND			42	V
	Clamping voltage <sup>(4)</sup>	I <sub>PP</sub> = 16 A, TLP, from IO to GND		33		
V <sub>Hold</sub>	Holding voltage after snapback <sup>(2)</sup>			28.5		V
I <sub>LEAK</sub>	Leakage current, any IO pin to GND	V <sub>IO</sub> = ±24 V	-50	1	50	nA
n	Dynamic resistance <sup>(4)</sup>	IO to GND		0.35		Ω
R <sub>DYN</sub> Dynamic resistance <sup>(4)</sup>		GND to IO		0.35		12
<u> </u>	Line conscitance any IO to CND	V <sub>IO</sub> = 0 V, f = 1 MHz, V <sub>p-p</sub> = 30 mV		3	5	pF
C <sub>L</sub>	Line capacitance, any IO to GND	V <sub>IO</sub> = 2.5 V, f = 1 MHz, V <sub>p-p</sub> = 30 mV		2.5	5	pF

<sup>(1)</sup> V<sub>BRF</sub> and V<sub>BRR</sub> are defined as the voltage when 1 mA is applied in the positive-going direction, before the device latches into the snapback state.

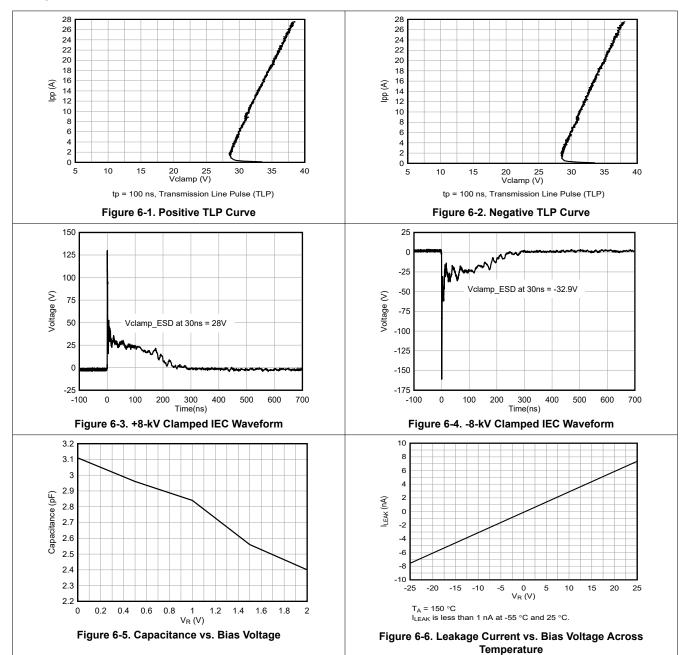
<sup>(2)</sup> V<sub>HOLD</sub> is defined as the voltage when 1 mA is applied in the negative-going direction, after the device has successfully latched into the snapback state.

<sup>(3)</sup> Device stressed with 8/20 μs exponential decay waveform according to IEC 61000-4-5.

<sup>(4)</sup> Non-repetitive current pulse, Transmission Line Pulse (TLP); square pulse; ANSI / ESD STM5.5.1-2008.



## 6.8 Typical Characteristics





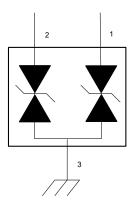
## 7 Detailed Description

#### 7.1 Overview

The ESD2CAN24-Q1 is a dual-channel ESD TVS diode in SOT-23 and SC-70 leaded packages which are convenient for automatic optical inspection. This product offers ISO ±30-kV air-gap, ±30-kV contact ESD protection, and has a clamp circuit with a back-to-back TVS diode for bidirectional signal support. The 3 pF line capacitance of this ESD protection diode is suitable for CAN, CANFD, CAN SiC, and CAN-XL applications that can support data rates up to 10 Mbps.

Typical application of this product is the ESD circuit protection for CAN transceivers used in automotive applications. The ESD2CAN24-Q1 is a good fit for the ESD protection inside automotive electronic control units (ECUs) for head lights, door modules, climate control, roof control, wipers, cluster, audio, and many other automotive applications.

### 7.2 Functional Block Diagram



#### 7.3 Feature Description

The ESD2CAN24-Q1 is a bidirectional TVS with a high ESD protection level. This device protects the circuit from ESD strikes up to  $\pm 30$ -kV contact and  $\pm 30$ -kV air-gap specified in the ISO 10605 automotive standard. The device can also handle up to 3.5 A surge current (IEC 61000-4-5 8/20  $\mu$ s). The I/O capacitance of 3-pF supports a data rate up to 10 Mbps. This clamping device has a small dynamic resistance, which makes the clamping voltage low when the device is actively protecting other circuits. For example, the clamping voltage is only 31 V when the device is taking 3.5 A transient current. The breakdown is bidirectional so this protection device is a good fit for CAN which is a differential signal. Low leakage allows the diode to conserve power when working below the  $V_{RWM}$ . The temperature range of -55°C to +150°C makes this ESD device work at extensive temperatures in most environments. The leaded SOT-23 and SC-70 packages are good for applications requiring automatic optical inspection (AOI).

#### 7.3.1 AEC-Q101 Qualified and Temperature Range

This device is qualified to AEC-Q101 standards and is qualified to operate from -55°C to +150°C.

#### 7.3.2 ISO 10605 ESD Protection

The I/O pins can withstand ESD events of at least  $\pm 30$ -kV contact and  $\pm 30$ -kV air-gap in the leaded SOT-23 and SC-70 packages according to the ISO 10605 (330 pF and 330  $\Omega$  loading condition) standard. An ESD-surge clamp diverts the current to ground.

#### 7.3.3 IEC 61000-4-5 Surge Protection

The IO pins can withstand surge events up to 3.5 A (8/20  $\mu$ s waveform). An ESD-surge clamp diverts this current to ground.

#### 7.3.4 IO Capacitance

The capacitance between the I/O pins is 3 pF. This capacitance supports data rates for CAN, CANFD, CAN SiC, and CAN-XL up to 10 Mbps.



#### 7.3.5 Dynamic Resistance

The IO pins feature an ESD clamp that has a low  $R_{DYN}$  of 0.35  $\Omega$  (Pin 1 or Pin 2 to Pin 3) and 0.35  $\Omega$  (Pin 3 to Pin 1 or Pin 2) which prevents system damage during ESD events.

#### 7.3.6 DC Breakdown Voltage

The DC breakdown voltage between the IO pins is a minimum of  $\pm$  25.5 V. This ensures that sensitive equipment is protected from surges above the reverse standoff voltage of  $\pm$  24 V.

#### 7.3.7 Ultra Low Leakage Current

The IO pins feature an ultra-low leakage current of 50 nA (maximum) with a bias of ± 24 V.

#### 7.3.8 Clamping Voltage

The IO pins feature an ESD clamp that is capable of clamping the voltage to 31 V ( $I_{PP}$  = 3.5 A) and 33 V ( $I_{PP}$  = 16 A for TLP).

## 7.3.9 Industry Standard Leaded Packages

This device features industry standard SOT-23 (DBZ) and SC-70 (DCK) leaded packages for automatic optical inspection (AOI).

#### 7.4 Device Functional Modes

The ESD2CAN24-Q1 is a dual channel passive clamp that has low leakage during normal operation when the voltage between pin 1 or pin 2 and pin 3 is below  $V_{RWM}$ , and activates when the voltage between pin 1 or pin 2 and pin 3 goes above  $V_{BR}$ . During ISO ESD events, transient voltages as high as  $\pm 30$  kV can be clamped on either channel. When the voltages on the protected lines fall below the  $V_{HOLD}$ , the device reverts back to the low leakage passive state.

Submit Document Feedback

Copyright © 2022 Texas Instruments Incorporated



## 8 Application and Implementation

#### Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

#### 8.1 Application Information

The ESD2CAN24-Q1 is a dual channel TVS diode which is used to provide a path to ground for dissipating ESD events on differential CAN signal lines. The CAN signal lines are typically routed throughout the automobile to connect between the different ECUs. As the current from ESD passes through the TVS, only a small voltage drop is present across the diode. This is the voltage presented to the protected IC. The low  $R_{DYN}$  of the triggered TVS holds this voltage,  $V_{CLAMP}$ , to a safe level for the protected IC.

#### 8.2 Typical Application

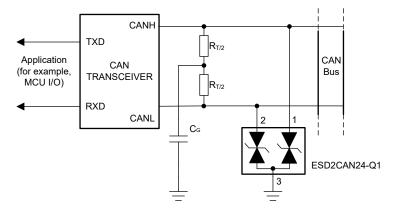


Figure 8-1. ESD2CAN24-Q1 Typical Application

#### 8.2.1 Design Requirements

For this design example, the ESD2CAN24-Q1 is used to provide ESD protection to a CAN transceiver. The parameters listed in Table 8-1 are the known design parameters for this application.

Table 8-1. Design Parameters for the ESD2CAN24-Q1 Typical Application

Design Parameter	Value	
Diode configuration	Bidirectional	
V <sub>IO</sub> differential signal range	> ±1.5 V	
V <sub>RWM</sub>	±24 V	
Jumpstart short to battery event on V <sub>IO</sub>	±24 V	
Data rate	Up to 10 Mbps	
RT/2	60 Ω	



#### 8.2.2 Detailed Design Procedure

The ESD2CAN24-Q1 has a  $V_{RWM}$  of ±24 V to protect the diode from being damaged during a short to battery event that can occur by reversing the terminal connections during jumpstart. The bidirectional characteristic ensures the differential CAN signal integrity is not impacted by the diode. The low capacitance of 3 pF ensures data rates up to 10 Mbps, which allows the designer to meet the requirements for CAN, CANFD, CAN SiC, and CAN-XL. The 60  $\Omega$  split termination improves the electromagnetic emissions behavior of the network by filtering higher-frequency common-mode noise that may be present on the differential signal lines.

## 9 Power Supply Recommendations

This device is a passive TVS diode-based ESD protection device, therefore there is no requirement to power it. Ensure that the maximum voltage specifications for each pin are not violated.

#### 10 Layout

## 10.1 Layout Guidelines

- The optimum placement is as close to the connector as possible.
  - EMI during an ESD event can couple from the trace being struck to other nearby unprotected traces, resulting in early system failures.
  - The PCB designer must minimize the possibility of EMI coupling by keeping any unprotected traces away from the protected traces which are between the TVS and the connector.
- Route the protected traces as straight as possible.
- Eliminate any sharp corners on the protected traces between the TVS and the connector by using rounded corners with the largest radii possible.
  - Electric fields tend to build up on corners, increasing EMI coupling.
- If pin 1, 2, or pin 3 is connected to ground, use a thick and short trace for this return path.

## 10.2 Layout Example

This application is typical of a differential data pair application, such as CAN.

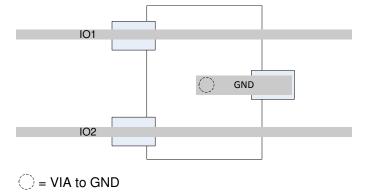


Figure 10-1. Routing with DBZ and DCK Package

Submit Document Feedback

Copyright © 2022 Texas Instruments Incorporated



## 11 Device and Documentation Support

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed below.

#### 11.1 Documentation Support

#### 11.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, ESD Layout Guide user's guide
- Texas Instruments, ESD Protection Diodes EVM user's guide
- Texas Instruments, Generic ESD Evaluation Module user's guide
- Texas Instruments, Reading and Understanding an ESD Protection data sheet

### 11.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Subscribe to updates* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

#### 11.3 Support Resources

TI E2E<sup>™</sup> support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

#### 11.4 Trademarks

TI E2E<sup>™</sup> is a trademark of Texas Instruments.

All trademarks are the property of their respective owners.

#### 11.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

#### 11.6 Glossary

TI Glossary

This glossary lists and explains terms, acronyms, and definitions.

#### 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

Copyright © 2022 Texas Instruments Incorporated

**DBZ0003A** 

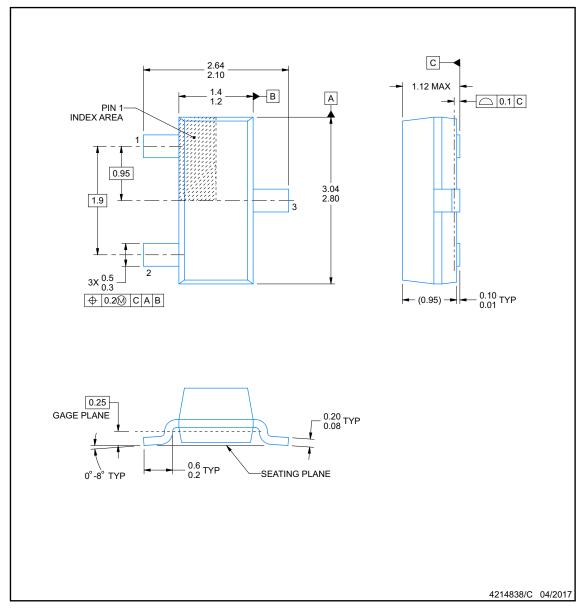




## **PACKAGE OUTLINE**

## SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



#### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
   This drawing is subject to change without notice.
   Reference JEDEC registration TO-236, except minimum foot length.





## **EXAMPLE BOARD LAYOUT**

## **DBZ0003A**

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR PKG 3X (1.3) 3X (0.6) SYMM 2X (0.95) (R0.05) TYP LAND PATTERN EXAMPLE SCALE:15X -SOLDER MASK OPENING SOLDER MASK-OPENING METAL UNDERSOLDER MASK METAL -0.07 MAX ALL AROUND 0.07 MIN ALL AROUND NON SOLDER MASK SOLDER MASK DEFINED (PREFERRED) SOLDER MASK DETAILS 4214838/C 04/2017

NOTES: (continued)

- 4. Publication IPC-7351 may have alternate designs.
- 5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



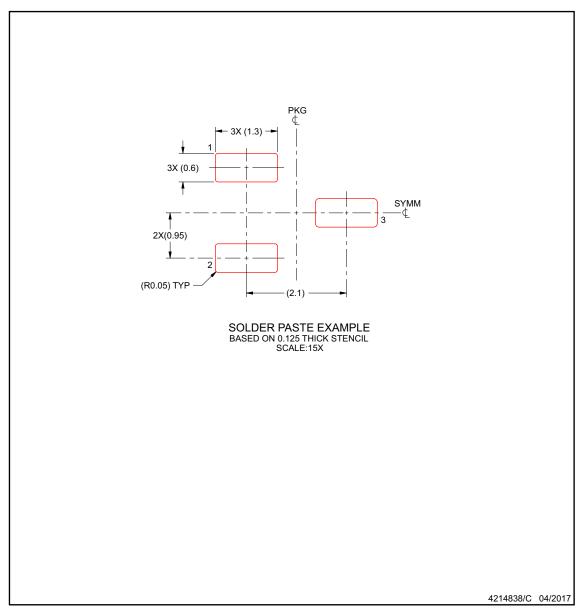


## **EXAMPLE STENCIL DESIGN**

# **DBZ0003A**

SOT-23 - 1.12 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

- 6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

  7. Board assembly site may have different recommendations for stencil design.





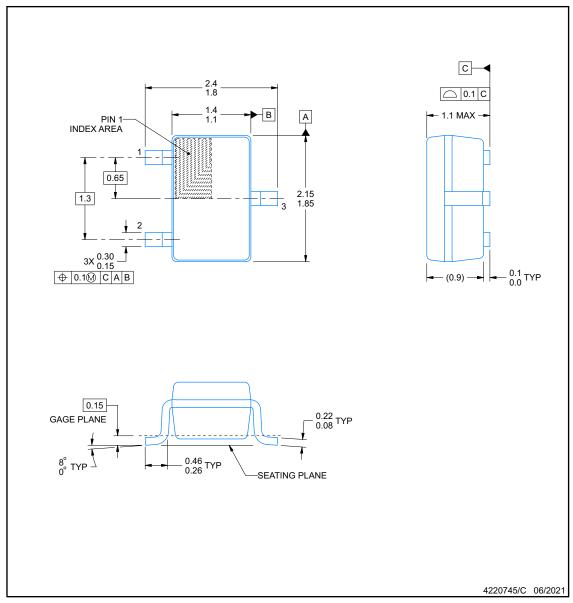
**DCK0003A** 



## PACKAGE OUTLINE

## SOT-SC70 - 1.1 max height

SMALL OUTLINE TRANSISTOR SC70



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.



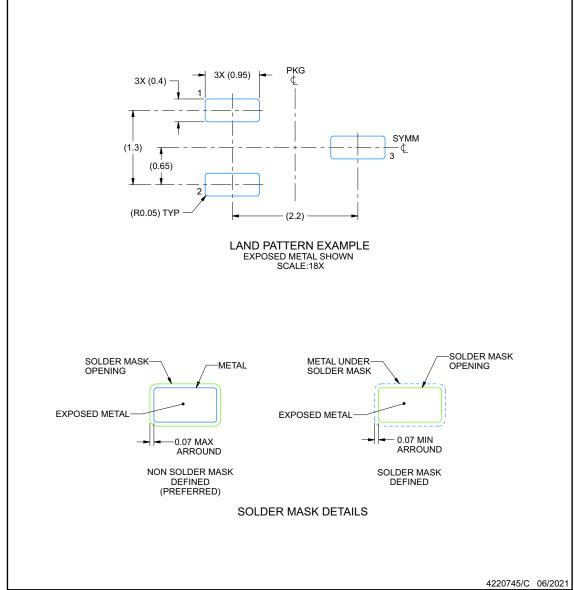


## **EXAMPLE BOARD LAYOUT**

# **DCK0003A**

SOT-SC70 - 1.1 max height

SMALL OUTLINE TRANSISTOR SC70



NOTES: (continued)

- 3. Publication IPC-7351 may have alternate designs.
- 4. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

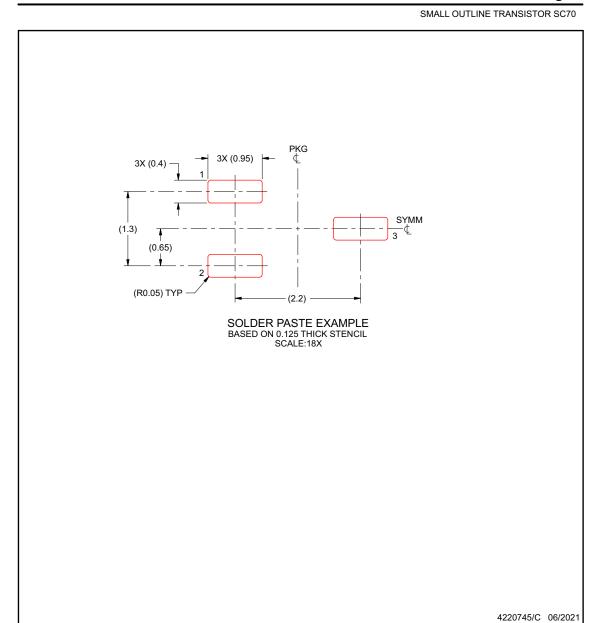




## **EXAMPLE STENCIL DESIGN**

# **DCK0003A**

SOT-SC70 - 1.1 max height



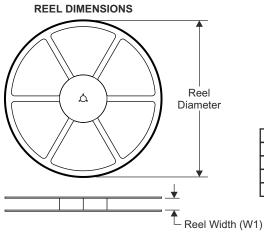
NOTES: (continued)

- 5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.6. Board assembly site may have different recommendations for stencil design.





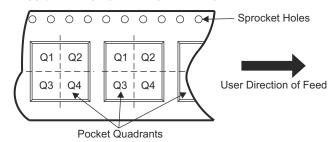
## 12.1 Tape and Reel Information



# **TAPE DIMENSIONS** Ф Ф B<sub>0</sub>

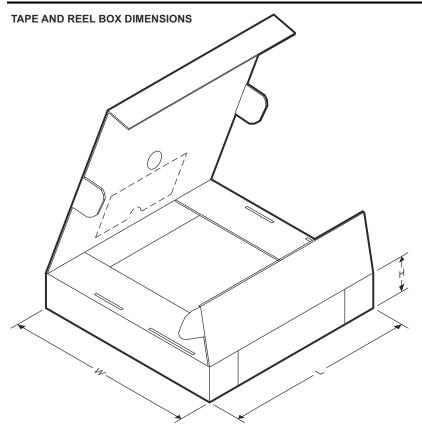
A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers
	•

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
PESD2CAN24DBZRQ1	SOT-23	DBZ	3	3000	180.0	8.4	2.9	3.35	1.35	4.0	8	Q3
PESD2CAN24DCKRQ1	SC-70	DCK	3	3000	180.0	8.4	2.9	3.35	1.35	4.0	5.30	Q3





Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
PESD2CAN24DBZRQ1	SOT-23	DBZ	3	3000	210.0	185.0	35.0
PESD2CAN24DCKRQ1	SC-70	DCK	3	3000	210.0	185.0	35.0

www.ti.com 9-Jun-2022

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
PESD2CAN24DBZRQ1	ACTIVE	SOT-23	DBZ	3	3000	TBD	Call TI	Call TI	-55 to 150		Samples
PESD2CAN24DCKRQ1	ACTIVE	SC70	DCK	3	3000	TBD	Call TI	Call TI	-55 to 150		Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

**Important Information and Disclaimer:** The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



# **PACKAGE OPTION ADDENDUM**

www.ti.com

## IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI's products are provided subject to TI's Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI's provision of these resources does not expand or otherwise alter TI's applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265 Copyright © 2022, Texas Instruments Incorporated